

isc Silicon NPN Power Transistor

2SC4467

**DESCRIPTION**

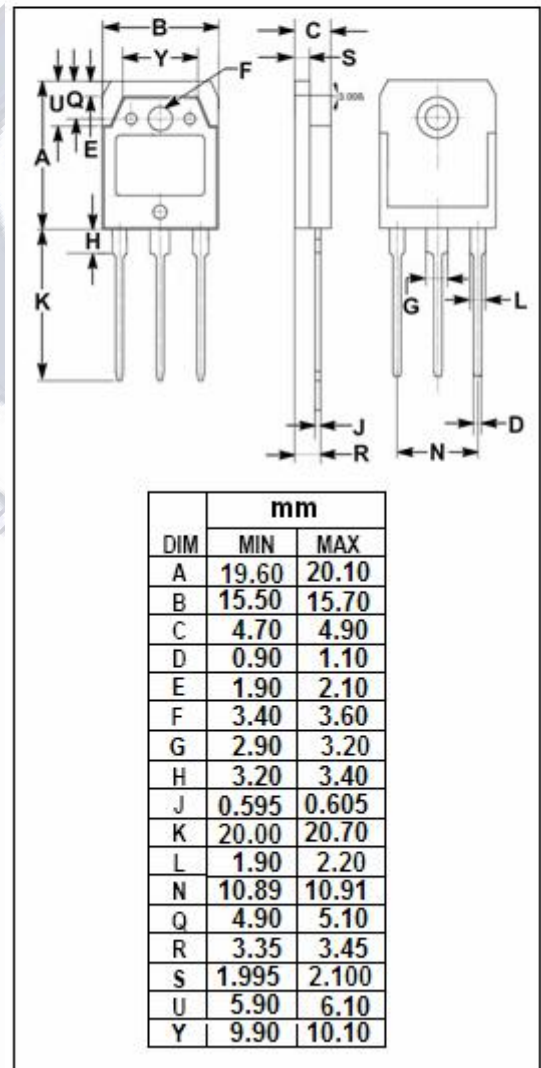
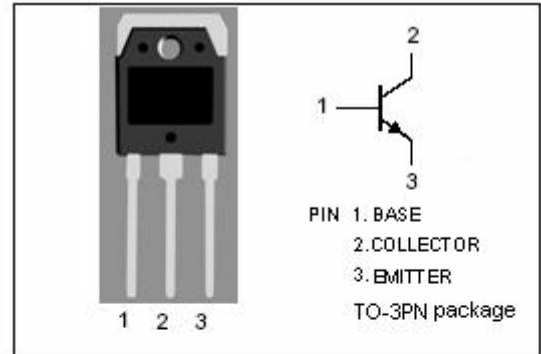
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = 120V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SA1694
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for audio and general purpose applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	160	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC4467****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=160\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=3\text{A}; V_{CE}=4\text{V}$	50		180	
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$		200		pF
$f_T$	Current-Gain—Bandwidth Product	$I_E=-0.5\text{A}; V_{CE}=12\text{V}$		20		MHz

## Switching Times

$t_{on}$	Turn-on Time	$I_C=4\text{A}, R_L=10\Omega,$ $I_{B1}=-I_{B2}=0.4\text{A}, V_{CC}=40\text{V}$		0.13		$\mu\text{s}$
$t_{stg}$	Storage Time			3.5		$\mu\text{s}$
$t_f$	Fall Time			0.32		$\mu\text{s}$

◆  $h_{FE}$  Classifications

O	P	Y
50-100	70-140	90-180